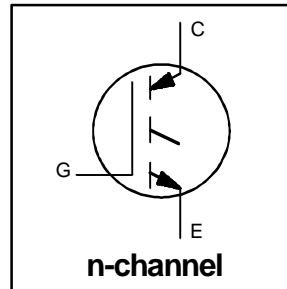


**INSULATED GATE BIPOLAR TRANSISTOR**

Short Circuit Rated  
UltraFast IGBT

**Features**

- Short circuit rated - 10 $\mu$ s @ 125°C, V<sub>GE</sub> = 15V
- Switching-loss rating includes all "tail" losses
- Optimized for high operating frequency (over 5kHz)  
See Fig. 1 for Current vs. Frequency curve

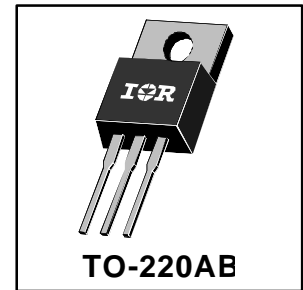


V <sub>CES</sub> = 600V
V <sub>CE(sat)</sub> ≤ 3.5V
@V <sub>GE</sub> = 15V, I <sub>C</sub> = 6.0A

**Description**

Insulated Gate Bipolar Transistors (IGBTs) from International Rectifier have higher usable current densities than comparable bipolar transistors, while at the same time having simpler gate-drive requirements of the familiar power MOSFET. They provide substantial benefits to a host of high-voltage, high-current applications.

These new short circuit rated devices are especially suited for motor control and other applications requiring short circuit withstand capability.



**Absolute Maximum Ratings**

	Parameter	Max.	Units
V <sub>CES</sub>	Collector-to-Emitter Voltage	600	V
I <sub>C</sub> @ T <sub>C</sub> = 25°C	Continuous Collector Current	10	A
I <sub>C</sub> @ T <sub>C</sub> = 100°C	Continuous Collector Current	6.0	
I <sub>CM</sub>	Pulsed Collector Current ①	20	
I <sub>LM</sub>	Clamped Inductive Load Current ②	20	
t <sub>sc</sub>	Short Circuit Withstand Time	10	μs
V <sub>GE</sub>	Gate-to-Emitter Voltage	±20	V
E <sub>ARV</sub>	Reverse Voltage Avalanche Energy ③	5.0	mJ
P <sub>D</sub> @ T <sub>C</sub> = 25°C	Maximum Power Dissipation	60	W
P <sub>D</sub> @ T <sub>C</sub> = 100°C	Maximum Power Dissipation	24	
T <sub>J</sub>	Operating Junction and	-55 to +150	°C
T <sub>STG</sub>	Storage Temperature Range		
	Soldering Temperature, for 10 sec.	300 (0.063 in. (1.6mm) from case)	
	Mounting torque, 6-32 or M3 screw.	10 lbf•in (1.1N•m)	

**Thermal Resistance**

	Parameter	Min.	Typ.	Max.	Units
R <sub>θJC</sub>	Junction-to-Case	—	—	2.1	°C/W
R <sub>θCS</sub>	Case-to-Sink, flat, greased surface	—	0.50	—	
R <sub>θJA</sub>	Junction-to-Ambient, typical socket mount	—	—	80	
Wt	Weight	—	2 (0.07)	—	g (oz)

## Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

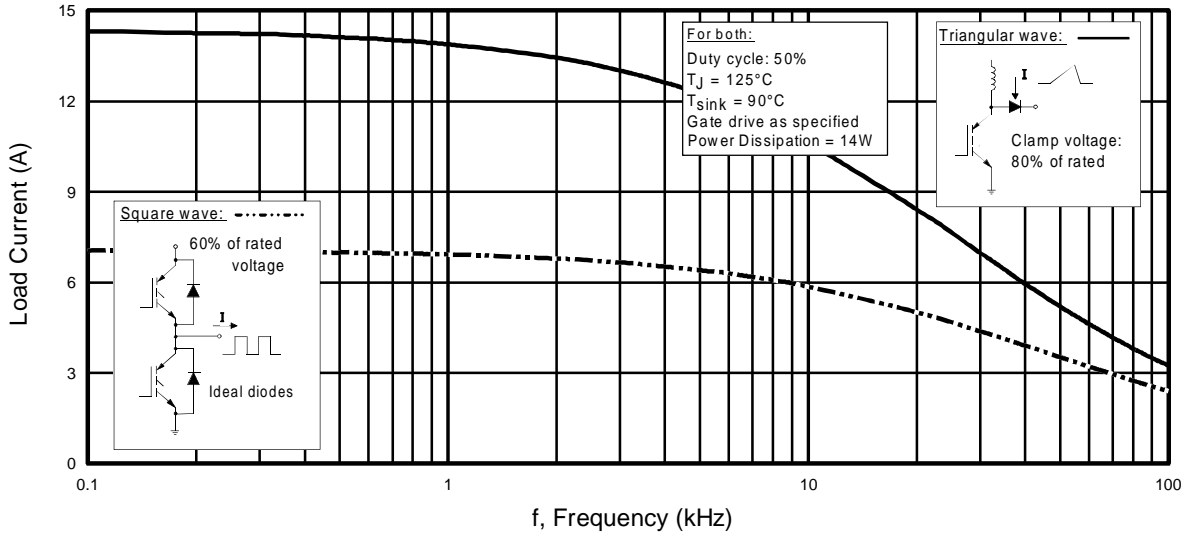
	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage	600	—	—	V	$V_{GE} = 0V, I_C = 250\mu\text{A}$
$V_{(BR)ECS}$	Emitter-to-Collector Breakdown Voltage ④	20	—	—	V	$V_{GE} = 0V, I_C = 1.0A$
$\Delta V_{(BR)CES}/\Delta T_J$	Temp. Coeff. of Breakdown Voltage	—	0.37	—	V/°C	$V_{GE} = 0V, I_C = 1.0mA$
$V_{CE(on)}$	Collector-to-Emitter Saturation Voltage	—	2.4	3.5	V	$I_C = 6.0A, V_{GE} = 15V$ See Fig. 2, 5
		—	3.6	—		
		—	2.9	—		
$V_{GE(th)}$	Gate Threshold Voltage	3.0	—	5.5		$V_{CE} = V_{GE}, I_C = 250\mu\text{A}$
$\Delta V_{GE(th)}/\Delta T_J$	Temperature Coeff. of Threshold Voltage	—	-11	—	mV/°C	$V_{CE} = V_{GE}, I_C = 250\mu\text{A}$
$g_{fe}$	Forward Transconductance ⑤	1.9	3.3	—	S	$V_{CE} = 100V, I_C = 6.0A$
$I_{CES}$	Zero Gate Voltage Collector Current	—	—	250	$\mu\text{A}$	$V_{GE} = 0V, V_{CE} = 600V$
		—	—	1000		
$I_{GES}$	Gate-to-Emitter Leakage Current	—	—	$\pm 100$	nA	$V_{GE} = \pm 20V$

## Switching Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

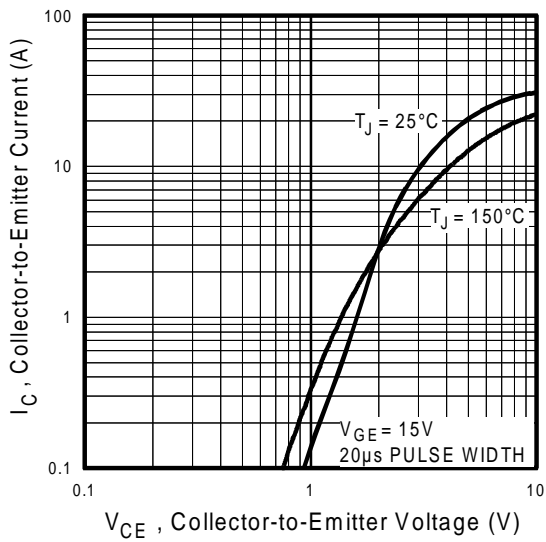
	Parameter	Min.	Typ.	Max.	Units	Conditions
$Q_g$	Total Gate Charge (turn-on)	—	17	26	nC	$I_C = 6.0A$ $V_{CC} = 400V$ See Fig. 8 $V_{GE} = 15V$
$Q_{ge}$	Gate - Emitter Charge (turn-on)	—	4.3	6.8		
$Q_{gc}$	Gate - Collector Charge (turn-on)	—	6.4	11		
$t_{d(on)}$	Turn-On Delay Time	—	29	—	ns	$T_J = 25^\circ\text{C}$ $I_C = 6.0A, V_{CC} = 480V$ $V_{GE} = 15V, R_G = 50\Omega$ Energy losses include "tail"
$t_r$	Rise Time	—	18	—		
$t_{d(off)}$	Turn-Off Delay Time	—	58	90		
$t_f$	Fall Time	—	120	200		
$E_{on}$	Turn-On Switching Loss	—	0.11	—	mJ	See Fig. 9, 10, 11, 14
$E_{off}$	Turn-Off Switching Loss	—	0.13	—		
$E_{ts}$	Total Switching Loss	—	0.24	0.31		
$t_{sc}$	Short Circuit Withstand Time	10	—	—	$\mu\text{s}$	$V_{CC} = 360V, T_J = 125^\circ\text{C}$ $V_{GE} = 15V, R_G = 50\Omega, V_{CPK} < 500V$
$t_{d(on)}$	Turn-On Delay Time	—	28	—	ns	$T_J = 150^\circ\text{C}$ , $I_C = 6.0A, V_{CC} = 480V$ $V_{GE} = 15V, R_G = 50\Omega$ Energy losses include "tail"
$t_r$	Rise Time	—	22	—		
$t_{d(off)}$	Turn-Off Delay Time	—	200	—		
$t_f$	Fall Time	—	145	—		
$E_{ts}$	Total Switching Loss	—	0.50	—	mJ	See Fig. 10, 14
$L_E$	Internal Emitter Inductance	—	7.5	—	nH	Measured 5mm from package
$C_{ies}$	Input Capacitance	—	360	—	pF	$V_{GE} = 0V$ $V_{CC} = 30V$ See Fig. 7 $f = 1.0MHz$
$C_{oes}$	Output Capacitance	—	45	—		
$C_{res}$	Reverse Transfer Capacitance	—	4.7	—		

### Notes:

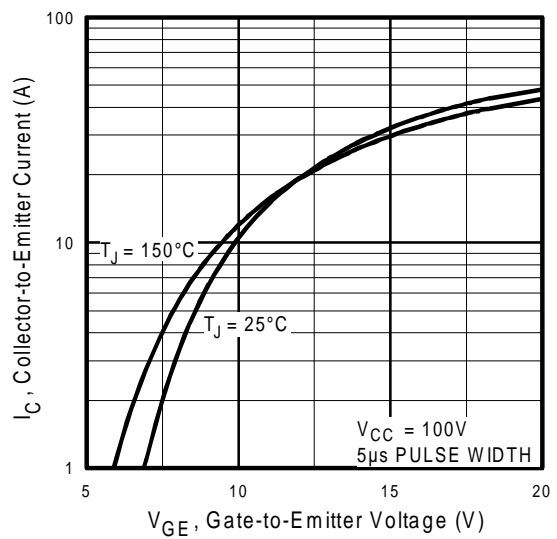
- ① Repetitive rating;  $V_{GE}=20V$ , pulse width limited by max. junction temperature. ( See fig. 13b )
- ②  $V_{CC}=80\%(V_{CES}), V_{GE}=20V, L=10\mu\text{H}, R_G=50\Omega$ , ( See fig. 13a )
- ③ Repetitive rating; pulse width limited by maximum junction temperature.
- ④ Pulse width  $\leq 80\mu\text{s}$ ; duty factor  $\leq 0.1\%$ .
- ⑤ Pulse width 5.0 $\mu\text{s}$ , single shot.



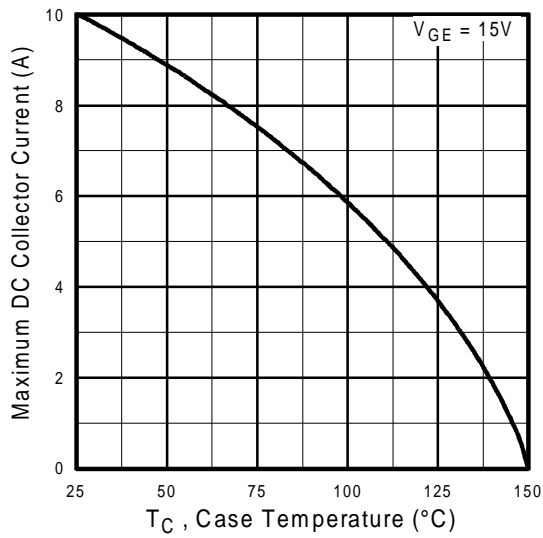
**Fig. 1 - Typical Load Current vs. Frequency**  
 (For square wave,  $I = I_{RMS}$  of fundamental; for triangular wave,  $I = I_{PK}$ )



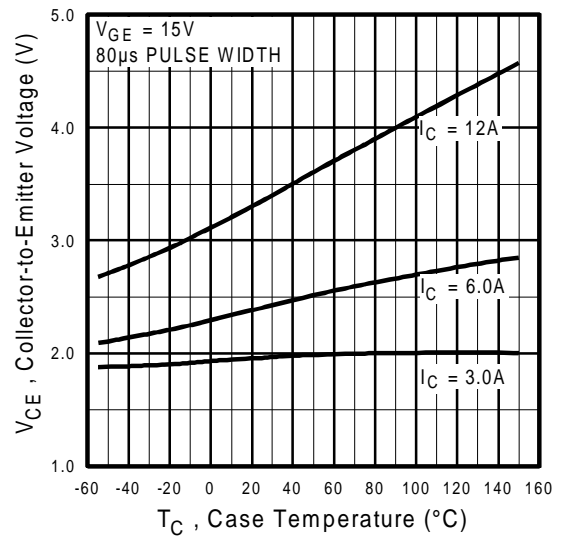
**Fig. 2 - Typical Output Characteristics**



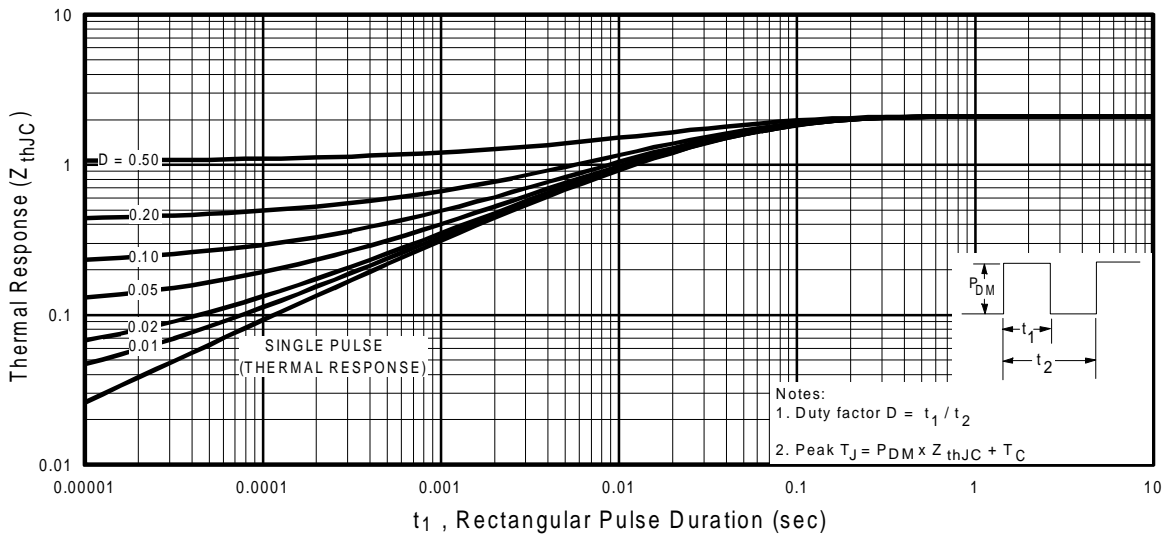
**Fig. 3 - Typical Transfer Characteristics**



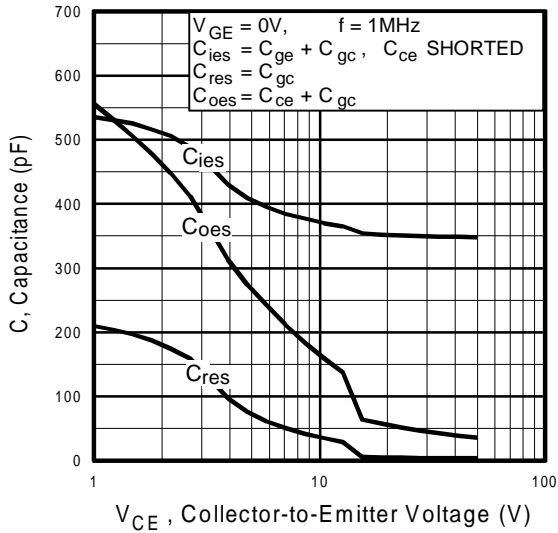
**Fig. 4 - Maximum Collector Current vs. Case Temperature**



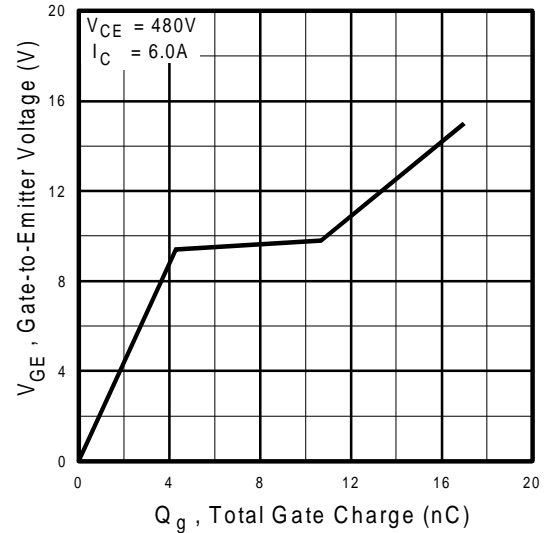
**Fig. 5 - Collector-to-Emitter Voltage vs. Case Temperature**



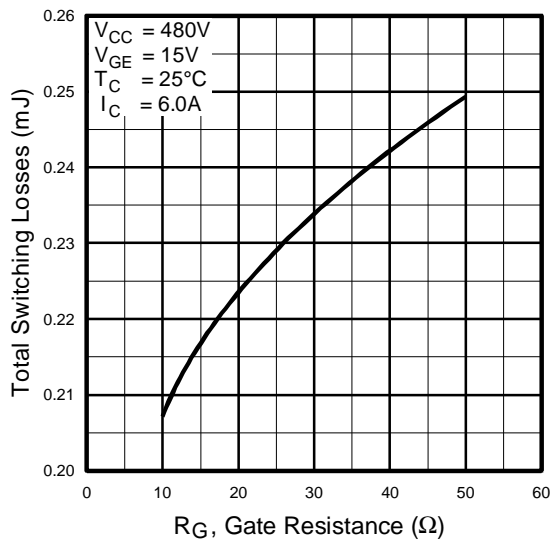
**Fig. 6 - Maximum Effective Transient Thermal Impedance, Junction-to-Case**



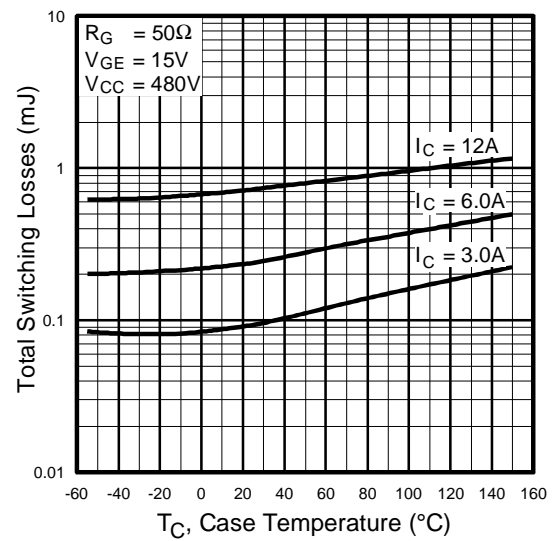
**Fig. 7** - Typical Capacitance vs. Collector-to-Emitter Voltage



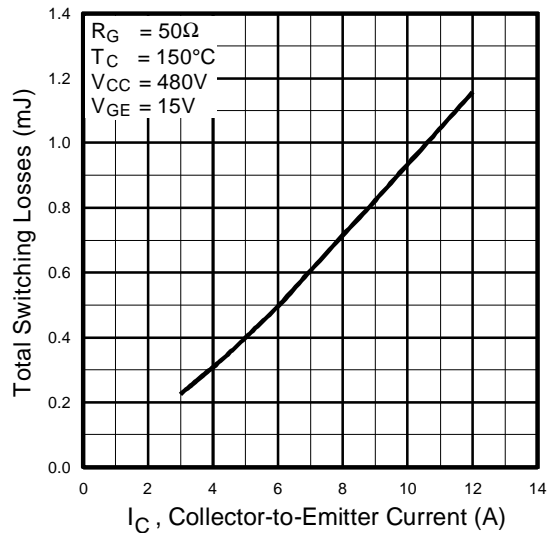
**Fig. 8** - Typical Gate Charge vs. Gate-to-Emitter Voltage



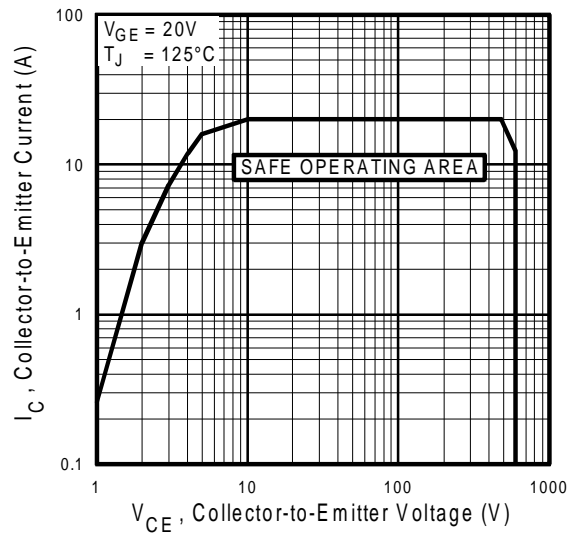
**Fig. 9** - Typical Switching Losses vs. Gate Resistance



**Fig. 10** - Typical Switching Losses vs. Case Temperature



**Fig. 11** - Typical Switching Losses vs. Collector-to-Emitter Current



**Fig. 12** - Turn-Off SOA

Refer to Section D for the following:

**Appendix C: Section D - page D-5**

Fig. 13a - Clamped Inductive Load Test Circuit

Fig. 13b - Pulsed Collector Current Test Circuit

Fig. 14a - Switching Loss Test Circuit

Fig. 14b - Switching Loss Waveform

Note: For the most current drawings please refer to the IR website at:  
<http://www.irf.com/package/>